

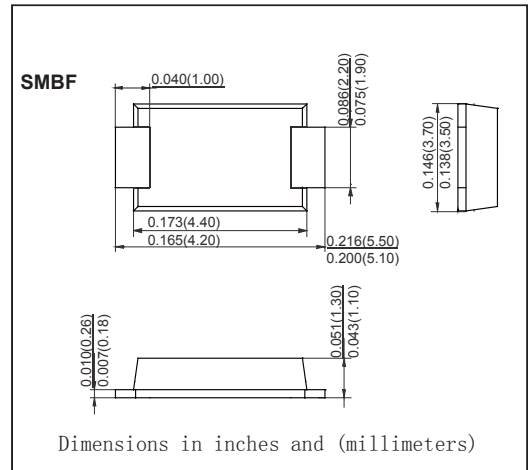
Schottky Barrier Rectifiers

FEATURES

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SMBF
- Terminals: Solderable per MIL-STD-750, Method 2026



MAXIMUM RATINGS AND CHARACTERISTICS

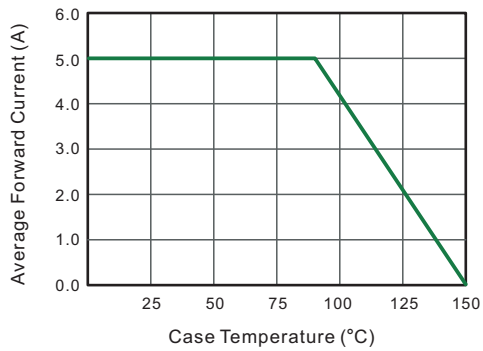
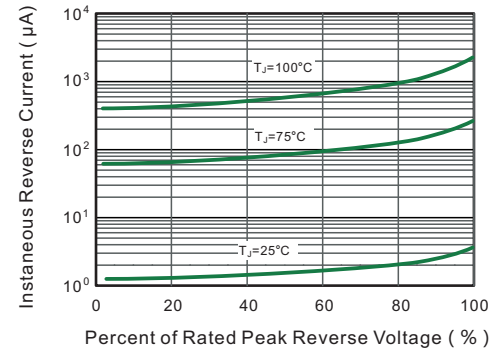
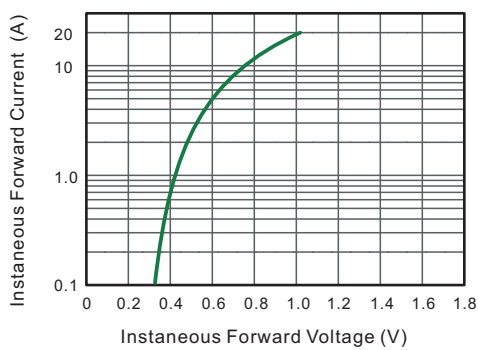
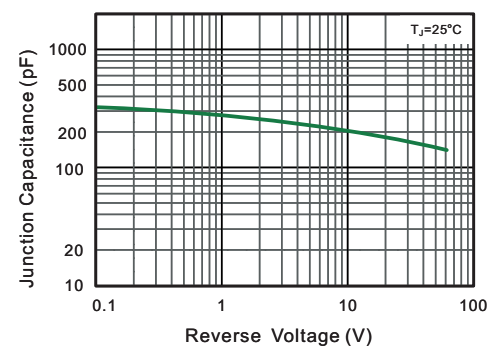
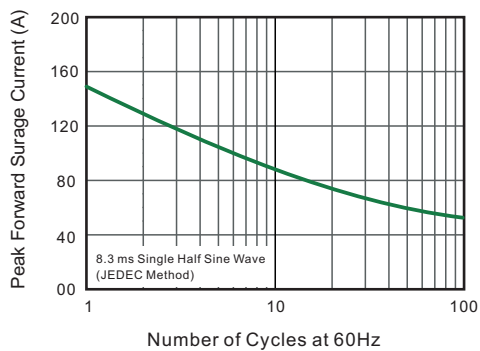
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbols	SS510L	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum RMS voltage	V_{RMS}	70	V
Maximum DC Blocking Voltage	V_{DC}	100	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	5.0	A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	150	A
Max Instantaneous Forward Voltage at 5 A	V_F	0.6	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Reverse Voltage	I_R	0.1	mA
Typical Junction Capacitance ⁽¹⁾	C_j	180	pF
Typical Thermal Resistance ⁽²⁾	$R_{\theta JA}$	60	°C/W
Operating Junction Temperature Range	T_j	-55 ~ +150	°C
Storage Temperature Range	T_{stg}	-55 ~ +150	°C

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

RATINGS AND CHARACTERISTIC CURVES

Fig.1 Forward Current Derating Curve

Fig.2 Typical Reverse Characteristics

Fig.3 Typical Forward Characteristic

Fig.4 Typical Junction Capacitance

Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

Fig.5- Typical Transient Thermal Impedance
